

2SB544/2SD400

Low-Frequency Power Amp, Electronic Governor Applications

Absolute Maximum Ratings at Ta=25°C

Collector to Base Voltage	V_{CBO}	(-)25	V
Collector to Emitter Voltage	V_{CEO}	(-)25	V
Emitter to Base Voltage	V_{EBO}	(-)5	V
Collector Current	I_C	(-)1	A
Collector Current(Pulse)	I_{CP}	(-)2	A
Collector Dissipation	P_C	900	mW
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55 to +150	$^{\circ}C$

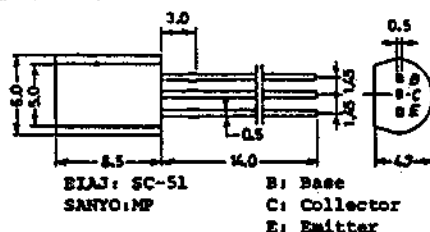
Electrical Characteristics at $T_a = 25^\circ\text{C}$

Electrical Characteristics at Ta = 25°C			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-)20V, I_E = 0$			$(-)1.0$	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			$(-)1.0$	μA
DC Current Gain	$h_{FE}(1)$	$V_{CE} = (-)2V, I_C = (-)50mA$	60※		560※	
	$h_{FE}(2)$	$V_{CE} = (-)2V, I_C = (-)1A$	30			
Gain-Bandwidth Product	f_T	$V_{CE} = (-)10V, I_C = (-)50mA$		180		MHz
Output Capacitance	c_{ob}	$V_{CB} = (-)10V, f = 1MHz$		(25)		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)500mA, I_E = (-)50mA$		15		
				0.1	0.3	
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)500mA, I_E = (-)50mA$				
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)25			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)25			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)5			V

*: The 2SB544/2SD400 are classified by 50mA h_{FE} as follows:

60	D	120	100	E	200	160	F	320	280	G	560
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Case Outline 2006A
(unit: mm)



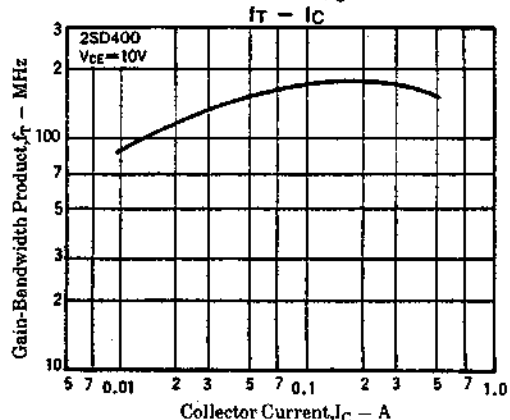
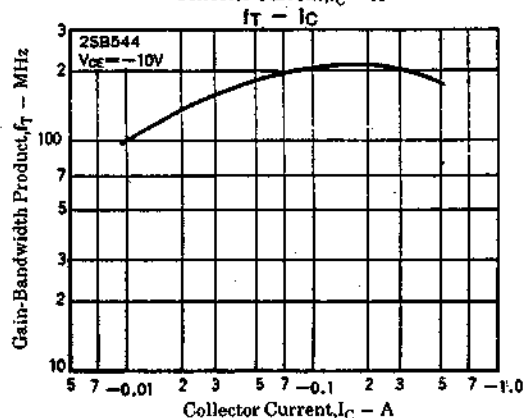
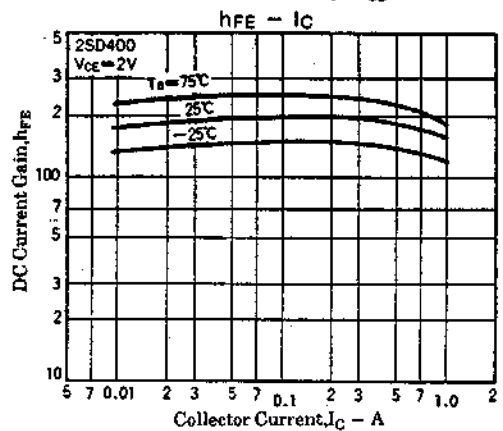
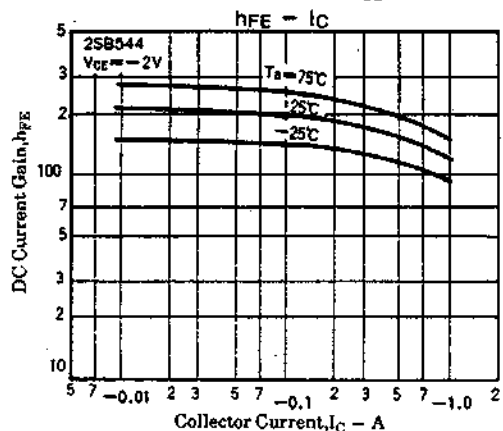
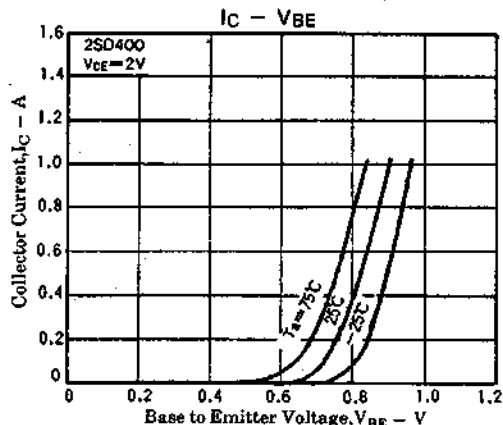
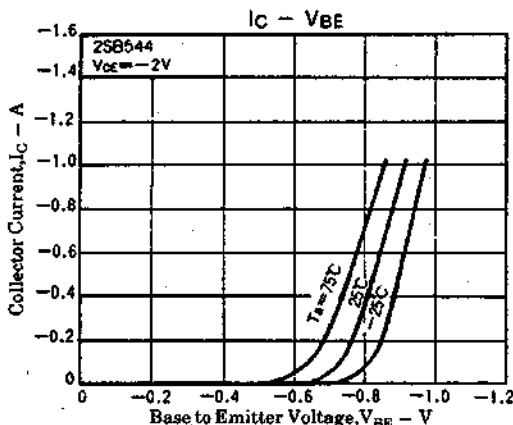
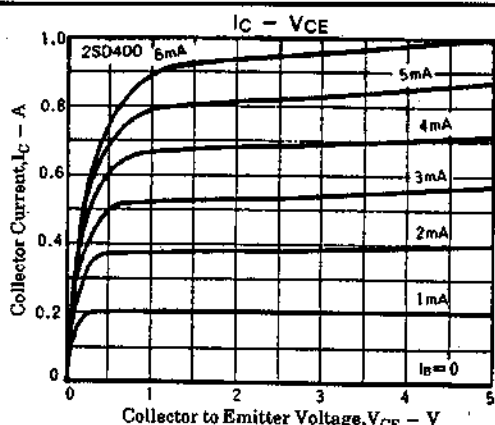
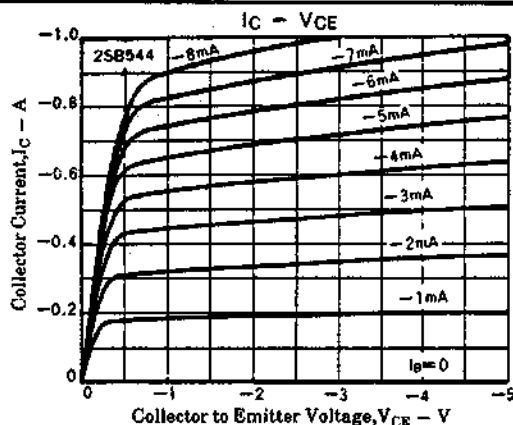
Specifications and information herein are subject to change without notice.

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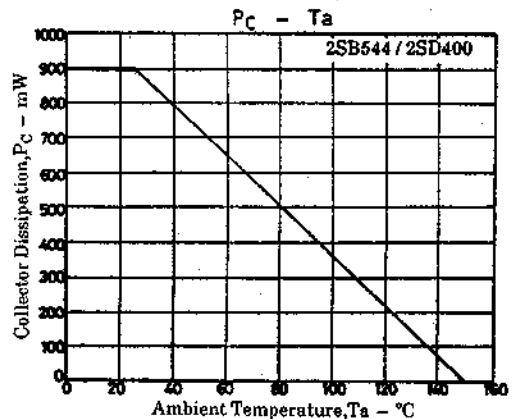
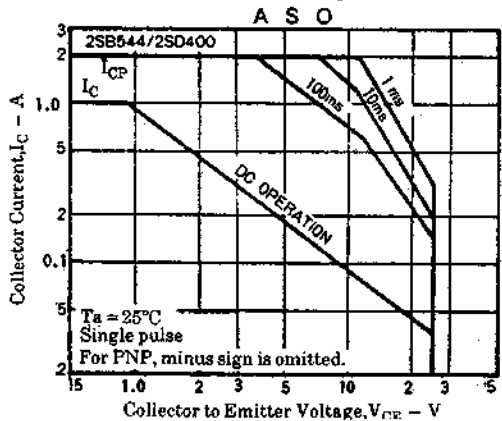
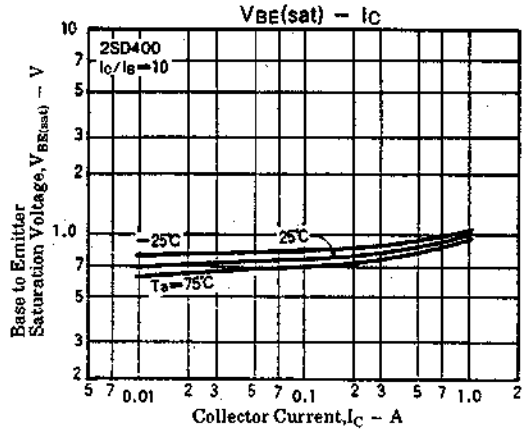
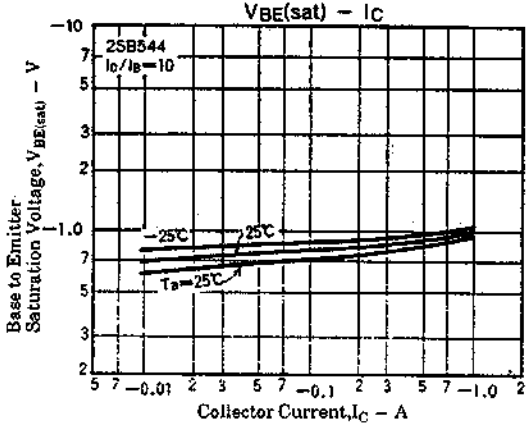
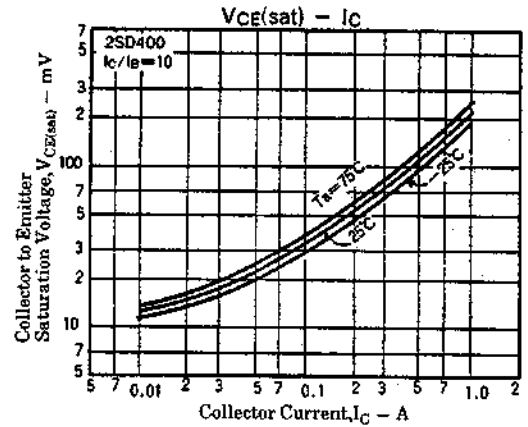
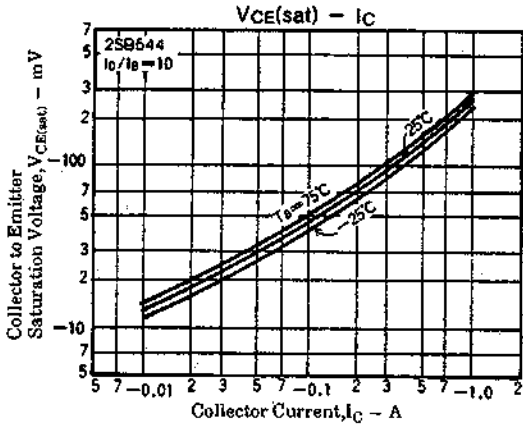
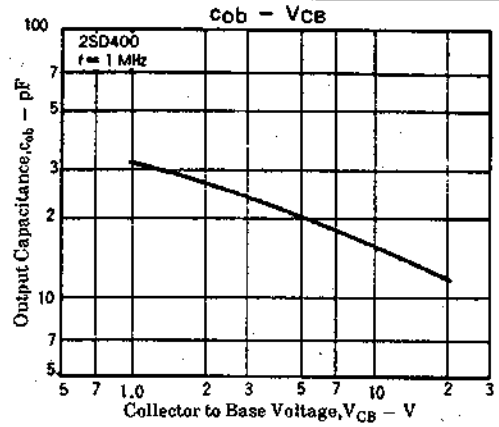
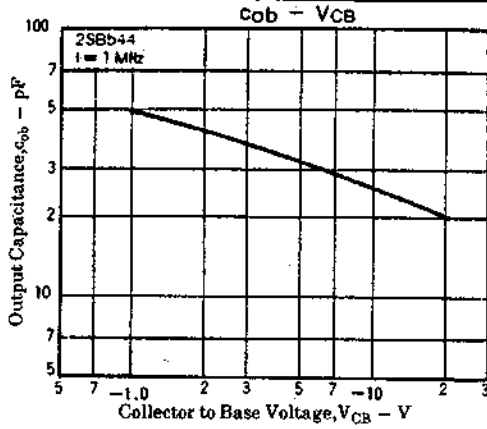
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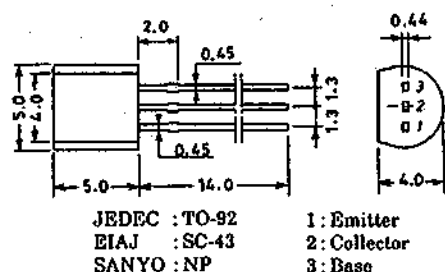
2SB544/2SD400



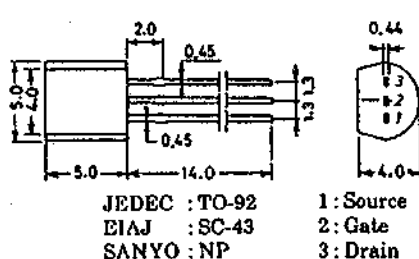
CASE OUTLINES OF LEAD FORMED SMALL SIGNAL TRANSISTORS

- All of Sanyo lead formed small signal transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

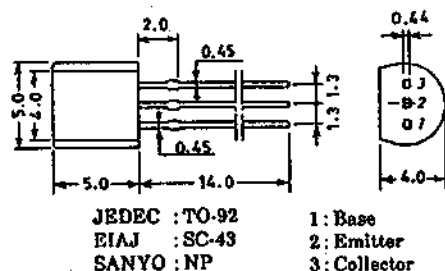
Case Outline 2003A/2003B (unit: mm)



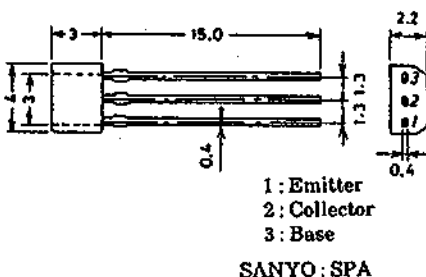
Case Outline 2019A/2019B (unit: mm)



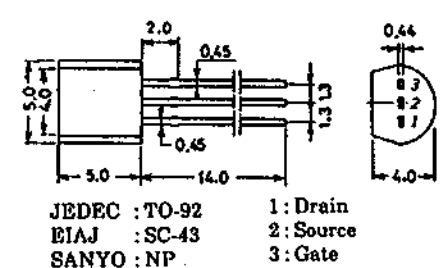
Case Outline 2004A (unit: mm)



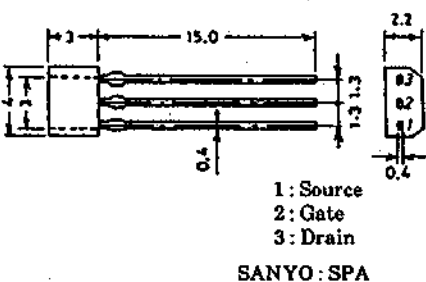
Case Outline 2033 (unit: mm)



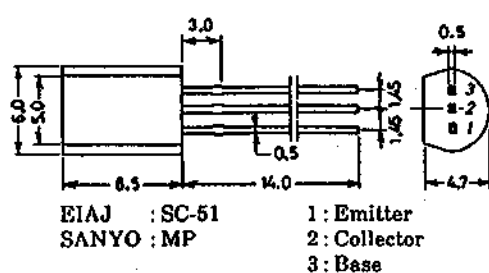
Case Outline 2005A (unit: mm)



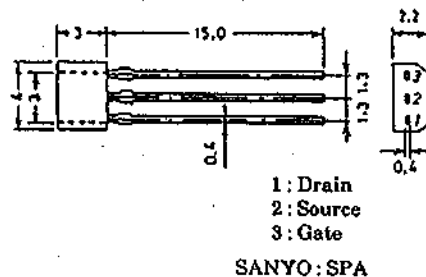
Case Outline 2034/2034A (unit: mm)



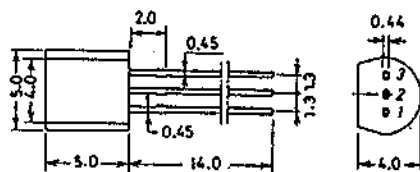
Case Outline 2006A (unit: mm)



Case Outline 2040 (unit: mm)



Case Outline 2061 (unit : mm)



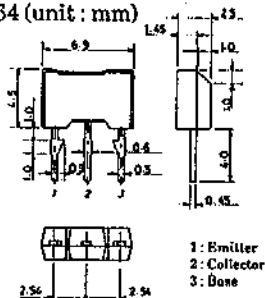
JEDEC : TO-92

EIAJ : SC-43

SANYO : NP

1: Emitter
2: Base
3: Collector

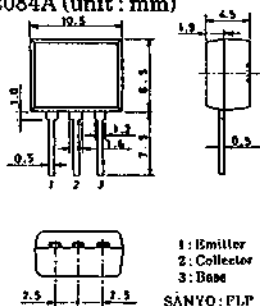
Case Outline 2064 (unit : mm)



1: Emitter
2: Collector
3: Base

SANYO : NMP

Case Outline 2084A (unit : mm)



1: Emitter
2: Collector
3: Base

SANYO : PLP

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